# **MMBTSA1576**

### **PNP Silicon Epitaxial Planar Transistor**

The transistor is subdivided into three groups Q, R and S according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.

# SOT-23 1.BASE 2.EMITTER 3.COLLECTOR

# SOT-23 Plastic Package

#### **Feature**

Excellent h<sub>FE</sub> linearity

#### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	-V <sub>CBO</sub>	60	V
Collector Emitter Voltage	-V <sub>CEO</sub>	50	V
Emitter Base Voltage	-V <sub>EBO</sub>	6	V
Collector Current	-I <sub>C</sub>	150	mA
Power Dissipation	P <sub>tot</sub>	200	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>S</sub>	-55 to +150	°C







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#### Characteristics at T<sub>amb</sub>=25 °C

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at $-V_{CE}=6V$ , $-I_{C}=1mA$	Q	h <sub>FE</sub>	120	-	270	-
	R	h <sub>FE</sub>	180	-	390	-
	S	h <sub>FE</sub>	270	-	560	-
Collector Cutoff Current						
at -V <sub>CB</sub> =60V		-I <sub>CBO</sub>	-	-	0.1	μA
Emitter Cutoff Current						
at -V <sub>EB</sub> =6V		-I <sub>EBO</sub>	-	-	0.1	μA
Collector Saturation Voltage						
at -I <sub>C</sub> =50mA, -I <sub>B</sub> =5mA		-V <sub>CE(sat)</sub>	-	-	0.5	V
Collector Base Breakdown Voltage						
at –I <sub>C</sub> =50µA		-V <sub>(BR)CBO</sub>	60	-	-	V
Collector Emitter Breakdown Voltage						
at -I <sub>C</sub> =1mA		-V <sub>(BR)CEO</sub>	50	-	-	V
Emitter Base Breakdown Voltage						
at -I <sub>E</sub> =50µA		-V <sub>(BR)EBO</sub>	6	-	-	V
Transition Frequency						
at -V <sub>CE</sub> =12V, -I <sub>E</sub> =2mA, f=30MHz		f⊤	-	140	-	MHz
Output Capacitance						
at –V <sub>CB</sub> =12V, f=1MHz		Cob		4.0	5	pF







